

Silicon Stabi Diode

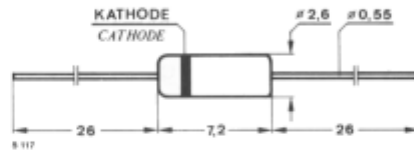
BZ102/2V1

2,1V / 250mA

DATASHEET

OEM – Telefunken

Source: Telefunken Databook 1977

BZ 102/...**Silizium-Diffusions-Stabilisator-Dioden**
Silicon diffusion voltage stabilising diodes**Anwendungen:** Spannungsstabilisierung und Spannungsbegrenzung**Applications:** Voltage stabilisation and voltage regulation**Abmessungen in mm**
Dimensions in mm

Normgehäuse
Case
51 A 2 DIN 41880
JEDEC DO 7
Gewicht · Weight
max. 0,3 g

Absolute Grenzdaten
Absolute maximum ratings

Durchlaßstrom Forward current	BZ 102/0 V 7	I_F	250	mA
	BZ 102/1 V 4	I_F	130	mA
	BZ 102/2 V 1	I_F	80	mA
	BZ 102/2 V 8	I_F	60	mA
	BZ 102/3 V 4	I_F	50	mA
Verlustleistung Power dissipation $l = 4 \text{ mm}, t_L \leq 45^\circ\text{C}$		P_V	250	mW
	Sperrschichttemperatur Junction temperature	t_j	150	°C
Lagerungstemperaturbereich Storage temperature range		t_{stg}	-55...+150	°C

Wärmewiderstand
Thermal resistance

	Min.	Typ.	Max.
Sperrschicht-Umgebung Junction ambient $l = 4 \text{ mm}, t_L = \text{konstant}$ constant			400 °C/W
			R_{thJA}

BZ 102/...

Kenngrößen
Characteristics

Min. Typ. Max.

$t_j = 25^\circ\text{C}$

Durchlaßspannung
Forward voltage

$I_F = 5\text{ mA}$

Part Number	Symbol	Min.	Typ.	Max.	Unit
BZ 102/0V7	U_F	0,65		0,75	V
BZ 102/1V4	U_F	1,3		1,5	V
BZ 102/2V1	U_F	1,9		2,3	V
BZ 102/2V8	U_F	2,6		3,0	V
BZ 102/3V4	U_F	3,2		3,7	V

Temperaturkoeffizient von U_F
Temperature coefficient of U_F

$I_F = 5\text{ mA}$

Symbol	Min.	Typ.	Max.	Unit
$-TK_{UF}$		23	$26 \cdot 10^{-4}$	/K

Sperrstrom
Reverse current

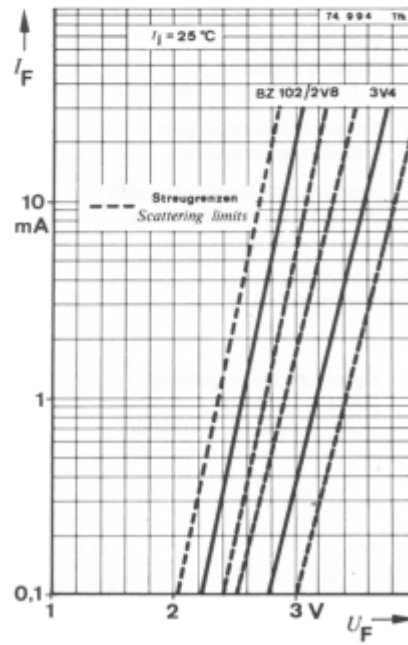
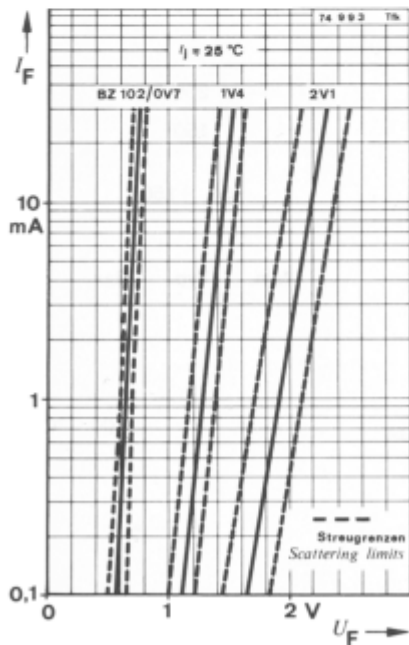
$U_R = 5\text{ V}$

Symbol	Min.	Typ.	Max.	Unit
I_R			1	μA

Differentieller Durchlaßwiderstand
Differential forward resistance

$I_F = 5\text{ mA}$

Part Number	Symbol	Min.	Typ.	Max.	Unit
BZ 102/0V7	r_f		6,5	10	Ω
BZ 102/1V4	r_f		13	20	Ω
BZ 102/2V1	r_f		19,5	30	Ω
BZ 102/2V8	r_f		26	40	Ω
BZ 102/3V4	r_f		32,5	50	Ω



BZ 102/...

